

AMENDMENTS TO THE CLAIMS

Claims 1-12 (Canceled)

Claim 13 (Newly Added): A magnetic memory unit, comprising:

a first magnetizable electrode;

a second magnetizable electrode; and

at least one nanotube arranged between the electrodes in a longitudinal direction and coupled to the first electrode by a first longitudinal end and to the second electrode by a second longitudinal end;

wherein a storage information item is stored in the memory unit in a nonvolatile fashion by setting a magnetization direction of one of the magnetizable electrodes by applying an external magnetic field.

Claim 14 (Newly Added): The magnetic memory unit as claimed in claim 13, wherein the nanotube is a carbon nanotube.

Claim 15 (Newly Added): The magnetic memory unit as claimed in claim 13, wherein the nanotube constitutes a quantum mechanical tunnel contact, with the spin state of charge carriers that flow between the two electrodes being at least partly preserved.



Claim 22 (Newly Added): The magnetic memory array as claimed in claim 20, wherein each of the second electrodes is coupled to a second interconnect, and the second electrodes are arranged along a line parallel to the second grid axis.

Claim 23 (Newly Added): The magnetic memory array as claimed in claim 20, wherein each of the first electrodes is formed as a common integral electrode, and the first electrodes are arranged along a line parallel to the first grid axis.

Claim 24 (Newly Added): The magnetic memory array as claimed in claim 20, wherein each of the second electrodes is formed as a common integral electrode, and the second electrodes are arranged along a line parallel to the second grid axis.